

1103 APD (Avalanche Photo Diode)

APD2001

800 nm to 1700 nm InGaAs Avalanche Photodiode



USE IN

- Ultra Weak Optical Detecting
- Optical Sensor OTDR
- Laser Lidar
- Laser Range Finding
- High Resolution Optical Coherence Tomography
- Scientific Analysis and Experiment

Photosurface (μm)	Response Wavelength (nm)	Responsivity (mA/mW@M=1)	Gain (1550 nm, 1 μW)	Reverse Breakdown Voltage (I _d =10 μA)	Dark Current (nA@M=100)
Φ30		0.8@1550	M=10@V _{br} -4 V M=20@V _{br} -2 V M=30@V _{br} -1.2 V	20 V to 50 V	0.5 nA @M=10
Φ50		0.9@1550		44±4 V	0.8 nA @M=10
Φ200	800 to 1700	0.9@1550 0.65@1064	M=10@V _{br} -4 V M=20@V _{br} -2 V M=30@V _{br} -1 V	45±10 V	10 nA @M=10
Φ500		0.9@1550 0.65@1064		45±10 V	130 nA @M=10